

RAYCONN ELECTRONICS CO., LTD.

SPECIFICATION FORM

FEATURES

- ✧ 0.8 INCHES (20.40MM) DIGIT HEIGHT
- ✧ 20.0MM×27.70MM OUTLINE
- ✧ SINGLE DIGIT
- ✧ SINGLE COLOR
- ✧ EASY ASSEMBLY
- ✧ HIGH BRIGHTNESS
- ✧ SOLID STATE RELIABILITY

DESCRIPTION

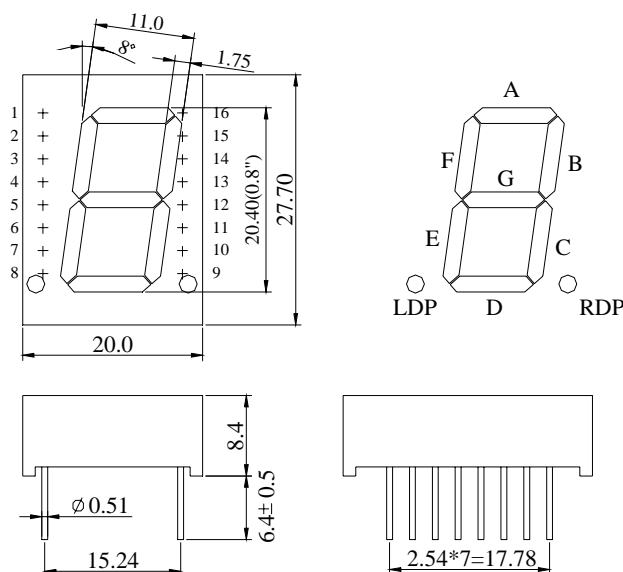
The REC-S8102AG is a 0.8 inches (20.40mm) digit height, 20.0mm×27.70mm outline, single color, single digit with common anode numeric display. The REC-S8102AG utilizes yellow-green LED chips fabricated from GaP epiwafer on GaP substrate grown by liquid phase epitaxy. These devices have black face and white segments.

DEVICE

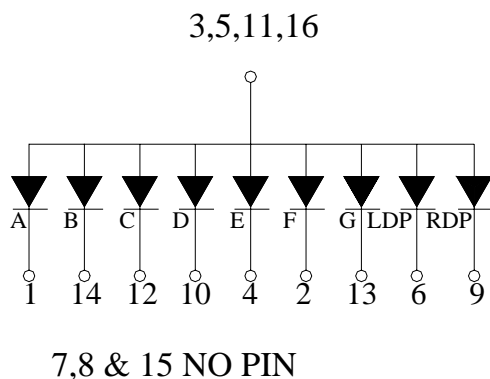
PART NO.	EMITTING COLOR	DESCRIPTION
REC-S8102AG	Yellow-Green	Black Surface & White Segments

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PACKAGE DIMENSION



INTERNAL CIRCUIT DIAGRAM



PIN CONNECTION

PIN NO.	CONNECTION	PIN NO.	CONNECTION
1	Cathode A	9	Cathode RDP
2	Cathode F	10	Cathode D
3	Common Anode	11	Common Anode
4	Cathode E	12	Cathode C
5	Common Anode	13	Cathode G
6	Cathode LDP	14	Cathode B
7	No Pin	15	No Pin
8	No Pin	16	Common Anode

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ABSOLUTE MAXIMUM RATING AT $T_A=25^\circ\text{C}$

PARAMETER	SYMBOL	MAXIMUM	UNIT
Power Dissipation per Seg.	P_{AD}	75	mW
Peak Forward Current per Seg.	I_{PF}	80	mA
Continuous Forward Current per Seg.	I_{AF}	20	mA
Reverse Voltage per Seg.	V_R	5	V
Operating Temperature Range, T_{opr}		- 25° C to + 60° C	
Storage Temperature Range, T_{stg}		- 30° C to + 85° C	
Solder Temperature : 1 / 16 inch below seating plane for 3 seconds at 260° C			

ELECTRO - OPTICAL CHARACTERISTICS AT $T_A=25^\circ\text{C}$

PARAMETER	UNIT	MIN	TYPE	MAX
Luminous Intensity per Seg., I_V ($I_F=20\text{mA}$)	mcd	8	11	14
Peak Emission Wavelength, λ_P ($I_F=20\text{mA}$)	nm		570	
Special Line Half-Width, $\Delta\lambda$ ($I_F=20\text{mA}$)	nm		30	
Forward Voltage per Seg., V_F ($I_F=20\text{mA}$)	V	2.0	2.1	2.2
Reverse Current per chipSeg., I_R , ($V_R=5\text{V}$)	μA			10
Luminous Intensity Matching Ratio, I_{V-m} ($I_F=20\text{mA}$)				2 : 1